

# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Application Number	10/575,625
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First Named Inventor	Hirimitsu SAKAI
Art Unit	2811
Examiner Name	Shouxiang HU
Attorney Docket Number	Q78084

## U.S. PATENTS

Examiner Initials*	Cite No	Patent Number	Kind Code <sup>1</sup>	Issue Date	Name of Patentee or Applicant of cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	1.	6242764	B1	2001-06-05	Ohba et al.	

## U.S. PATENT APPLICATION PUBLICATIONS

Examiner Initials*	Cite No	Publication Number	Kind Code <sup>1</sup>	Publication Date	Name of Patentee or Applicant of cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	2.	20030136333	A1	2003-07-24	Semond et al.	

## FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No	Foreign Document Number <sup>2</sup>	Country Code <sup>2</sup>	Kind Code <sup>3</sup>	Publication Date	Name of Patentee or Applicant of cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>5</sup>
	3.	1 160 882	EP	A2	2001-12-05	NGK INSULATORS, LTD.		

## NON-PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	T <sup>5</sup>
	4.	T. TAKEUCHI, ET AL: "Improvement of far-field pattern in nitride laser diodes", APPLIED PHYSICS LETTERS, AIP, AMERICAN INSTITUTE OF PHYSICS, MELVILLE, NY, US LNKD- DOI:10.1063/1.125201, vol. 75, no. 19, 8 November 1999 (1999-11-08), pages 2960-2962, XP012023940 ISSN: 0003-6951 * page 2960, column 2, line 8 - page 2961, column 1, line 8, figures 1, 2, 4 ** page 2962, column 1, lines 3-9 *	
	5.	C. ADELMAH, ET AL: "Atomic-layer epitaxy of GaN quantum wells and quantum dots on (0001) AlN", JOURNAL OF APPLIED PHYSICS, AMERICAN INSTITUTE OF PHYSICS, NEW YORK, US LNKD- DOI:10.1063/1.1458049, vol. 91, no. 8, 15 April 2002 (2002-04-15), pages 5498-5500, XP012056297 ISSN: 0021-8979 * page 5498, column 2, lines 7-9 ** page 5499, column 1, lines 14-28; figure 1b ** page 5499, column 2, line 26 - page 5500, column 1, line 9, figures 3a,b ** page 5500, column 2, lines 6-8, 13, 14 *	
	6.	M. MIYAMURA, ET AL: "Stranski-Krastanow growth of GaN quantum dots by metalorganic chemical vapor deposition", JOURNAL OF CRYSTAL GROWTH, ELSEVIER, AMSTERDAM, NL LNKD- DOI:10.1016/S0022-0248(01)02058-9, vol. 237-239, 1 April 2002 (2002-04-01), pages 1316-1319, XP004355989 ISSN: 0022-0248 * page 1317, column 1, lines 7-13 ** page 1317, column 1, line 20 - column 2, line 25; figures 2b, 2c, 3 ** page 1318, column 1, line 11 - page 1319, column 1, line 11; figure 4 *	
	7.	D. HUANG, ET AL: "Defect reduction with quantum dots in GaN grown on sapphire substrates by molecular beam epitaxy", APPLIED PHYSICS LETTERS, AIP, AMERICAN INSTITUTE OF PHYSICS, MELVILLE, NY, US LNKD- DOI:10.1063/1.1432445, vol. 80, no. 2, 14 January 2002 (2002-01-14), pages 216-218, XP012030887 ISSN: 0003-6951 * abstract ** page 216, column 2, line 36 - page 217, column 1, line 27 ** page 217, column 1, line 54 - page 218, column 1, line 26; figures 1-3 *	

## EXAMINER SIGNATURE

Examiner Signature	/Shouxiang Hu/	Date Considered	10/12/2010
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through a citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /S.H./